

# Central<sup>TM</sup> Semiconductor Corp.

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Manufacturers of World Class Discrete Semiconductors

CS202-4B  
CS202-4D  
CS202-4M

SILICON CONTROLLED RECTIFIER  
4.0 AMP, 200 THRU 600 VOLTS

JEDEC TO-202 CASE

## DESCRIPTION

The CENTRAL SEMICONDUCTOR CS202-4B series type is an Epoxy Molded Silicon Controlled Rectifier designed for sensing circuit applications and control systems.

MAXIMUM RATINGS ( $T_C=25^\circ\text{C}$  unless otherwise noted)

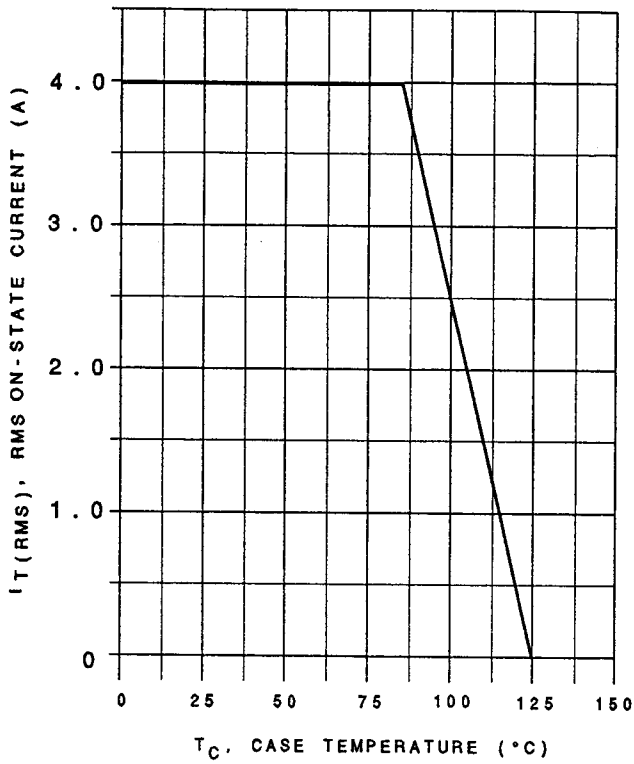
	<u>SYMBOL</u>	<u>CS202-4B</u>	<u>CS202-4D</u>	<u>CS202-4M</u>	<u>UNITS</u>
Peak Repetitive Off-State Voltage	$V_{DRM}, V_{RRM}$	200	400	600	V
RMS On-State Current ( $T_C=85^\circ\text{C}$ )	$I_T(\text{RMS})$		4.0		A
Peak One Cycle Surge ( $t=10\text{ms}$ )	$I_{TSM}$		30		A
$I^2t$ Value for Fusing ( $t=10\text{ms}$ )	$I^2t$		4.5		$\text{A}^2\text{s}$
Peak Gate Power ( $t_p=20\mu\text{s}$ )	$P_{GM}$		3.0		W
Average Gate Power Dissipation	$P_{G(AV)}$		0.2		W
Peak Gate Current ( $t_p=20\mu\text{s}$ )	$I_{GM}$		1.2		A
Critical Rate of Rise of On-State Current	$di/dt$		50		$\text{A}/\mu\text{s}$
Storage Temperature	$T_{stg}$		-40 to +150		$^\circ\text{C}$
Junction Temperature	$T_J$		-40 to +125		$^\circ\text{C}$
Thermal Resistance	$\Theta_{J-A}$		80		$^\circ\text{C}/\text{W}$
Thermal Resistance	$\Theta_{J-C}$		7.5		$^\circ\text{C}/\text{W}$

ELECTRICAL CHARACTERISTICS ( $T_C=25^\circ\text{C}$  unless otherwise noted)

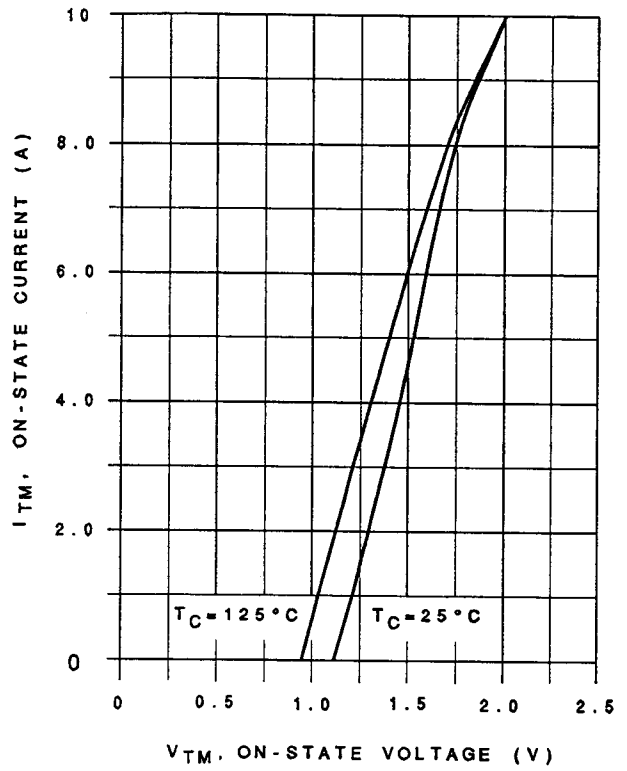
<u>SYMBOL</u>	<u>TEST CONDITIONS</u>	<u>MIN</u>	<u>TYP</u>	<u>MAX</u>	<u>UNITS</u>
$I_{DRM}, I_{RRM}$	Rated $V_{DRM}, V_{RRM}$ $R_{GK}=1\text{K}\Omega$			5.0	$\mu\text{A}$
$I_{DRM}, I_{RRM}$	Rated $V_{DRM}, V_{RRM}$ $R_{GK}=1\text{K}\Omega, T_C=110^\circ\text{C}$			200	$\mu\text{A}$
$I_{GT}$	$V_D=12\text{V}, R_L=140\Omega$	20		200	$\mu\text{A}$
$I_H$	$I_T=50\text{mA}, R_{GK}=1\text{K}\Omega$			5.0	mA
$V_{GT}$	$V_D=12\text{V}, R_L=140\Omega$			0.8	V
$V_{TM}$	$I_{TM}=8.0\text{A}$			1.8	V
$dv/dt$	$V_D=.67 \times V_{DRM}, R_{GK}=1\text{K}\Omega, T_C=110^\circ\text{C}$		20		$\text{V}/\mu\text{s}$

(OVER)

RMS ON-STATE CURRENT vs. CASE TEMPERATURE

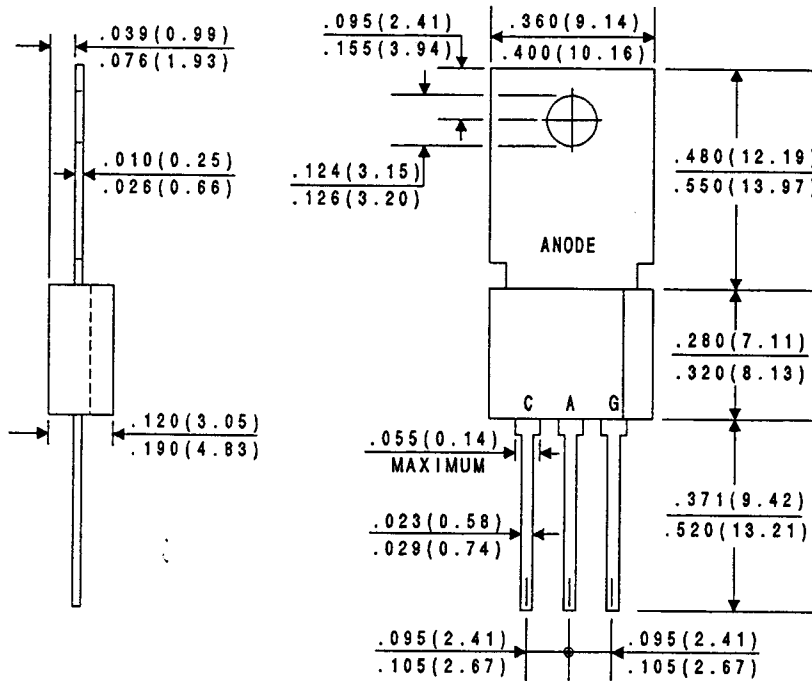


MAXIMUM ON-STATE CHARACTERISTICS



MECHANICAL OUTLINE

ALL DIMENSIONS IN INCHES (mm).



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